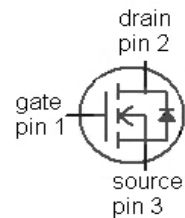
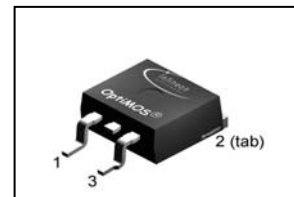


**OptiMOS<sup>®</sup> Power-Transistor**
**Features**

- N-channel Logic Level - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- **Green package (lead free)**
- Ultra low Rds(on)
- 100% Avalanche tested

**Product Summary**

|                                |    |    |
|--------------------------------|----|----|
| $V_{DS}$                       | 55 | V  |
| $R_{DS(on),max}$ (SMD version) | 35 | mΩ |
| $I_D$                          | 30 | A  |

**PG-TO252-3-11**


| Type           | Package       | Marking |
|----------------|---------------|---------|
| IPD26N06S2L-35 | PG-TO252-3-11 | 2N06L35 |

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

| Parameter                           | Symbol         | Conditions   | Value        | Unit |
|-------------------------------------|----------------|--|--------------|------|
| Continuous drain current            | $I_D$          | $T_C=25\text{ °C}$ , $V_{GS}=10\text{ V}$          | 30           | A    |
|                                     |                | $T_C=100\text{ °C}$ ,<br>$V_{GS}=10\text{ V}^{1)}$ | 22           |      |
| Pulsed drain current <sup>1)</sup>  | $I_{D,pulse}$  | $T_C=25\text{ °C}$                                 | 120          |      |
| Avalanche energy, single pulse      | $E_{AS}$       | $I_D=26\text{ A}$                                  | 80           | mJ   |
| Gate source voltage                 | $V_{GS}$       |  | ±20          | V    |
| Power dissipation                   | $P_{tot}$      | $T_C=25\text{ °C}$                                 | 68           | W    |
| Operating and storage temperature   | $T_j, T_{stg}$ |  | -55 ... +175 | °C   |
| IEC climatic category; DIN IEC 68-1 |                |  | 55/175/56    |      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|  |            |  |   |   |     |     |
|--|------------|--|---|---|-----|-----|
| Thermal resistance, junction - case            | $R_{thJC}$ |  | - | - | 2.2 | K/W |
| Thermal resistance, junction - ambient, leaded | $R_{thJA}$ |  | - | - | 100 |     |
| SMD version, device on PCB                     | $R_{thJA}$ | minimal footprint                            | - | - | 75  |     |
|  |            | 6 cm <sup>2</sup> cooling area <sup>2)</sup> | - | - | 50  |     |

**Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |   |     |      |     |               |
|----------------------------------|---------------|---|-----|------|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$  | 55  | -    | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=26\text{ }\mu\text{A}$                                  | 1.2 | 1.6  | 2.0 |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$       | -   | 0.01 | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}^{1)}$ | -   | 1    | 100 |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                                     | -   | 1    | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=4.5\text{ V}, I_D=13\text{ A}$                                      | -   | 34   | 47  | m $\Omega$    |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}, I_D=13\text{ A}$                                       | -   | 27   | 35  |               |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics<sup>1)</sup>**

|                              |              |  |   |     |   |    |
|------------------------------|--------------|--|---|-----|---|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$<br>$f=1\text{ MHz}$                   | - | 621 | - | pF |
| Output capacitance           | $C_{oss}$    |  | - | 178 | - |    |
| Reverse transfer capacitance | $C_{rss}$    |  | - | 63  | - |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=30\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=26\text{ A}, R_G=11\ \Omega$ | - | 5   | - | ns |
| Rise time                    | $t_r$        |  | - | 18  | - |    |
| Turn-off delay time          | $t_{d(off)}$ |  | - | 26  | - |    |
| Fall time                    | $t_f$        |  | - | 11  | - |    |

**Gate Charge Characteristics<sup>1)</sup>**

|                       |               |  |   |     |    |    |
|-----------------------|---------------|--|---|-----|----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=44\text{ V}, I_D=26\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 1   | 3  | nC |
| Gate to drain charge  | $Q_{gd}$      |  | - | 4   | 9  |    |
| Gate charge total     | $Q_g$         |  | - | 10  | 24 |    |
| Gate plateau voltage  | $V_{plateau}$ |  | - | 4.0 | -  | V  |

**Reverse Diode**

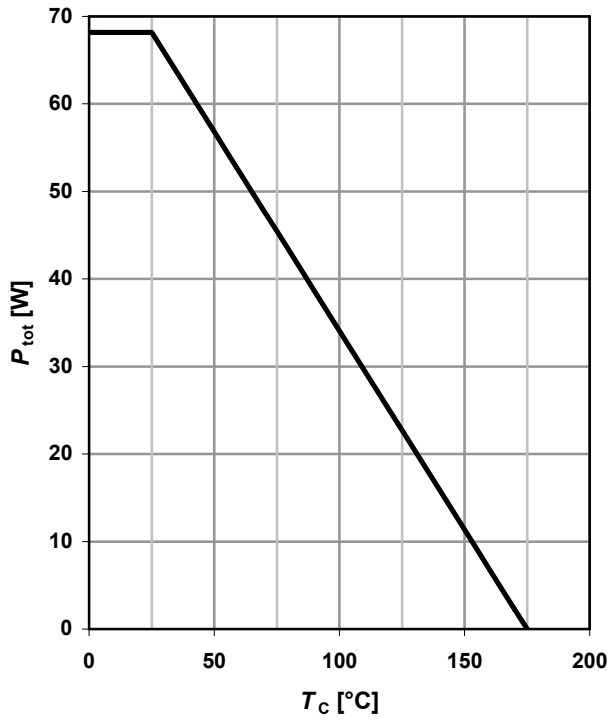
|  |               |   |   |      |     |    |
|--|---------------|---|---|------|-----|----|
| Diode continuous forward current <sup>1)</sup> | $I_S$         | $T_C=25\text{ }^\circ\text{C}$  | - | -    | 30  | A  |
| Diode pulse current <sup>1)</sup>              | $I_{S,pulse}$ |   | - | -    | 120 |    |
| Diode forward voltage                          | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=26\text{ A},$<br>$T_J=25\text{ }^\circ\text{C}$ | - | 0.95 | 1.3 | V  |
| Reverse recovery time <sup>1)</sup>            | $t_{rr}$      | $V_R=30\text{ V}, I_F=I_S,$<br>$di_F/dt=100\text{ A}/\mu\text{s}$       | - | 40   | -   | ns |
| Reverse recovery charge <sup>1)</sup>          | $Q_{rr}$      | $V_R=30\text{ V}, I_F=I_S,$<br>$di_F/dt=100\text{ A}/\mu\text{s}$       | - | 36   | -   | nC |

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

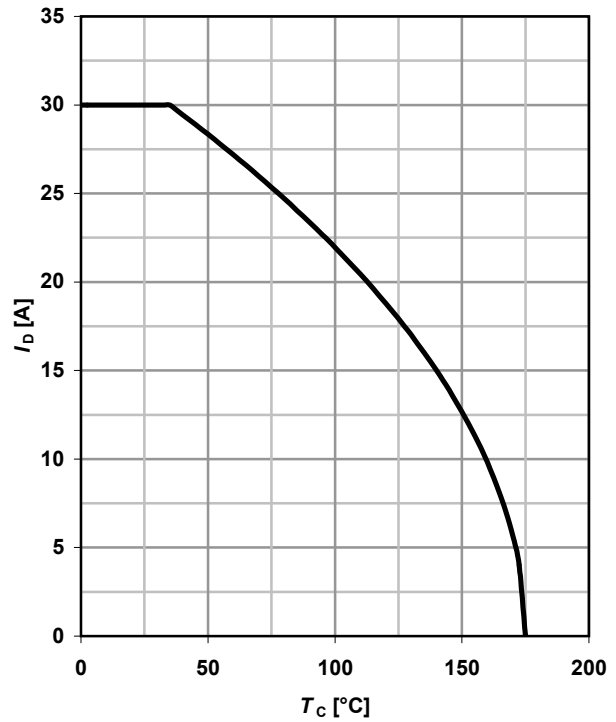
**1 Power dissipation**

$P_{tot} = f(T_C); V_{GS} \geq 6 V$



**2 Drain current**

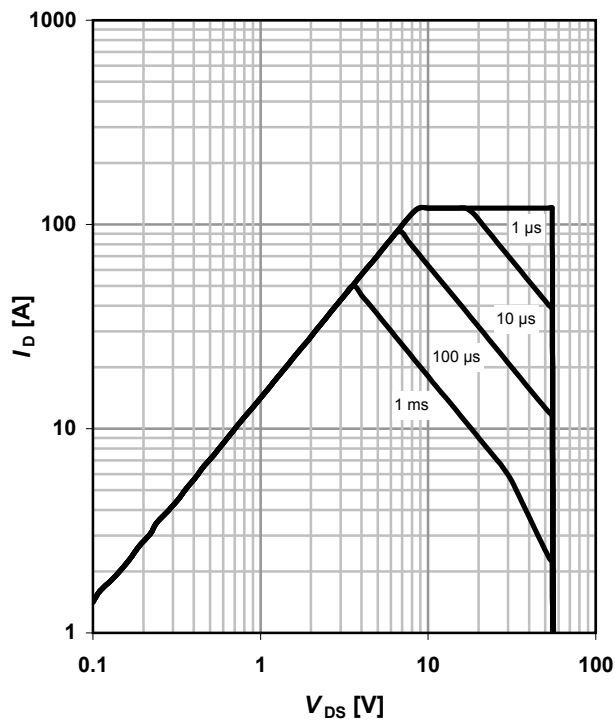
$I_D = f(T_C); V_{GS} \geq 10 V$



**3 Safe operating area**

$I_D = f(V_{DS}); T_C = 25\text{ °C}; D = 0$

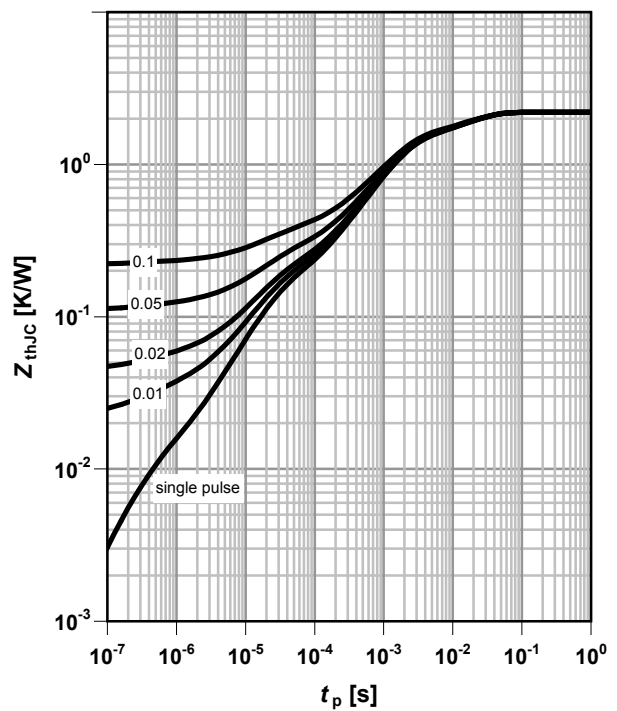
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC} = f(t_p)$

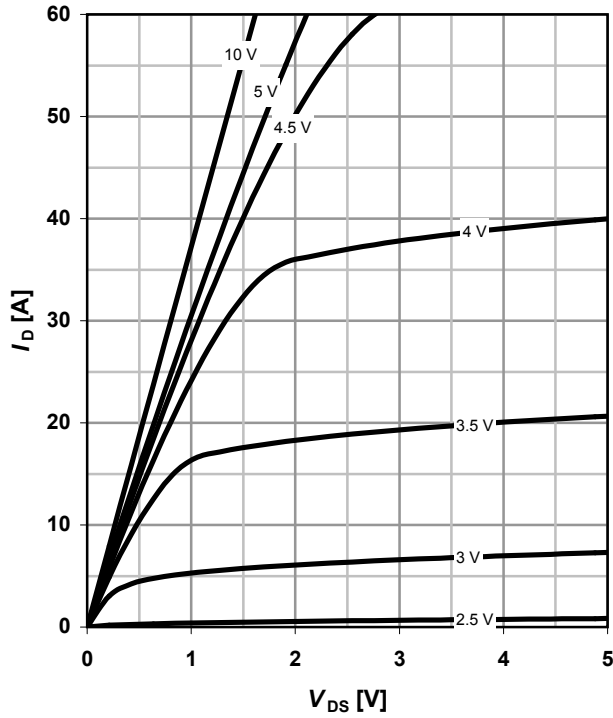
parameter:  $D = t_p/T$



### 5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

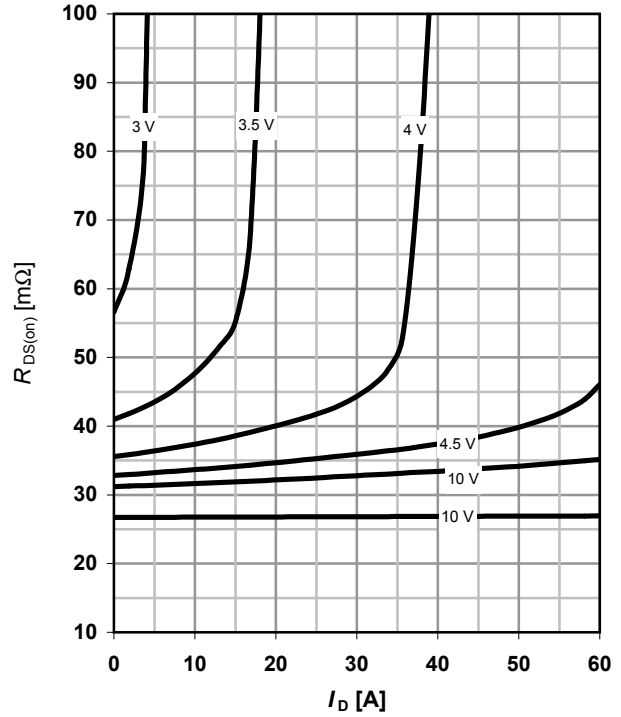
parameter:  $V_{GS}$



### 6 Typ. drain-source on-state resistance

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

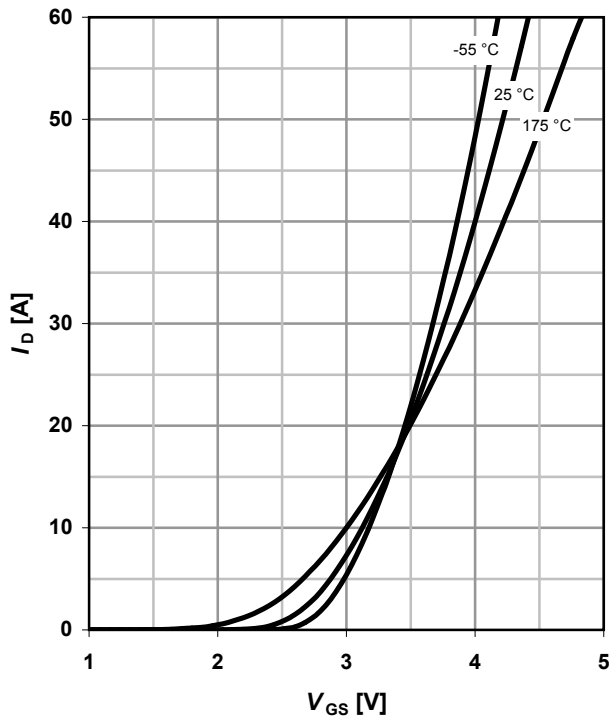
parameter:  $V_{GS}$



### 7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} = 6\text{V}$$

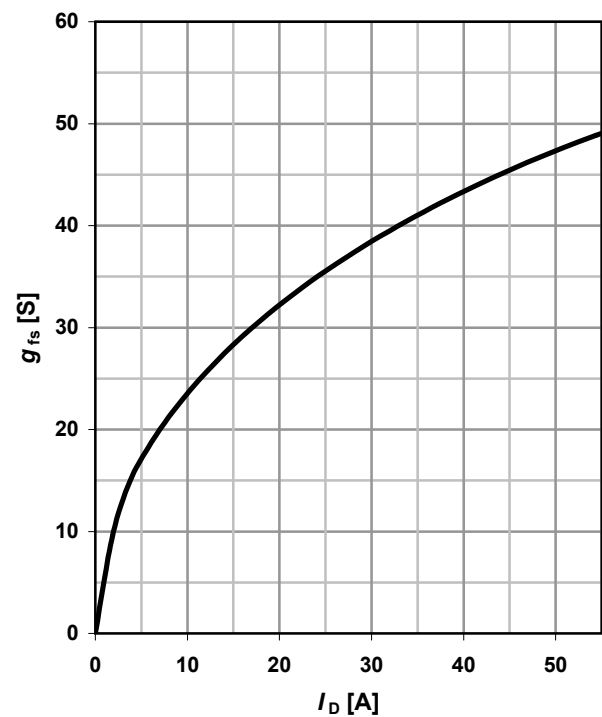
parameter:  $T_j$



### 8 Typ. Forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$

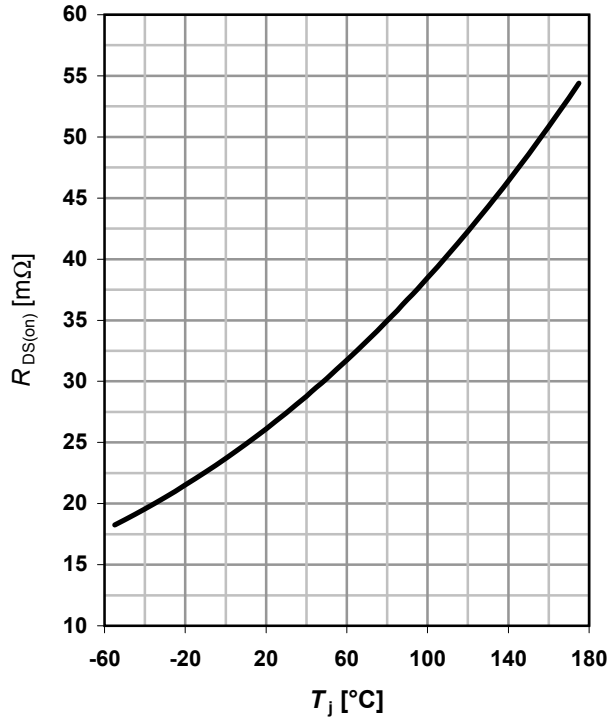
parameter:  $g_{fs}$



**9 Typ. Drain-source on-state resistance**

$R_{DS(ON)} = f(T_j)$

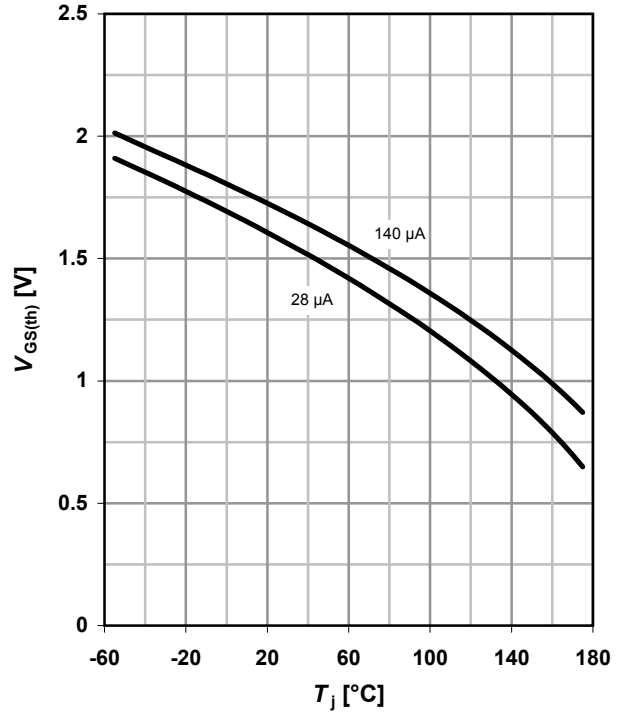
parameter:  $I_D = 13 \text{ A}$ ;  $V_{GS} = 10 \text{ V}$



**10 Typ. gate threshold voltage**

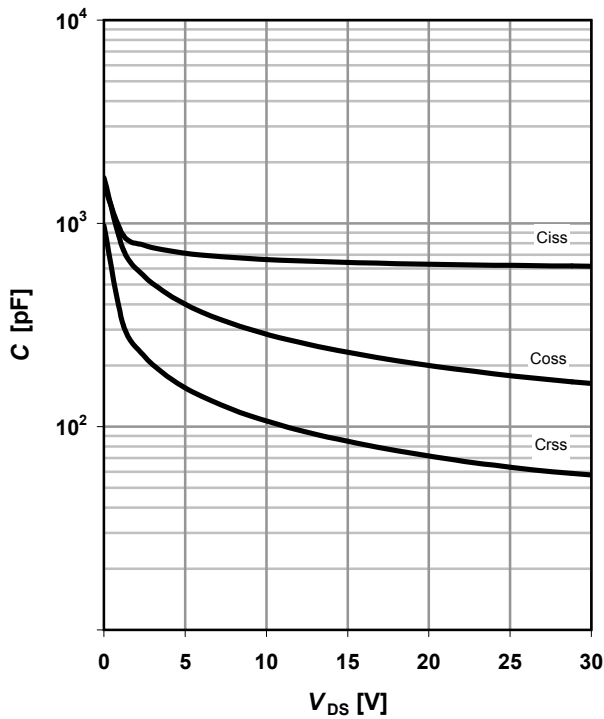
$V_{GS(th)} = f(T_j)$ ;  $V_{GS} = V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

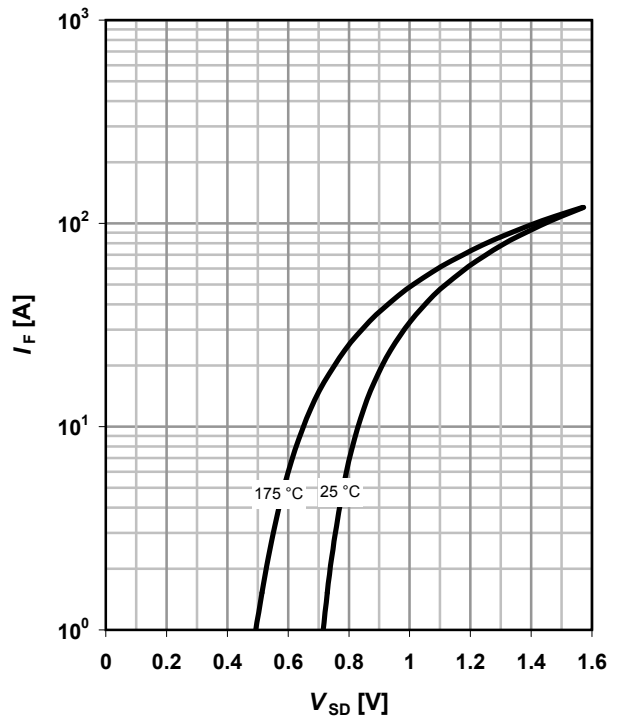
$C = f(V_{DS})$ ;  $V_{GS} = 0 \text{ V}$ ;  $f = 1 \text{ MHz}$



**12 Typical forward diode characteristics**

$I_F = f(V_{SD})$

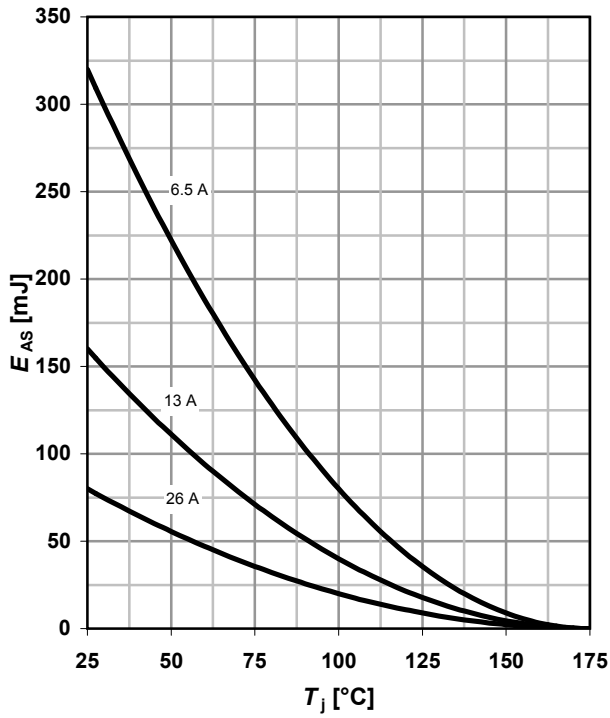
parameter:  $T_j$



**13 Typical avalanche energy**

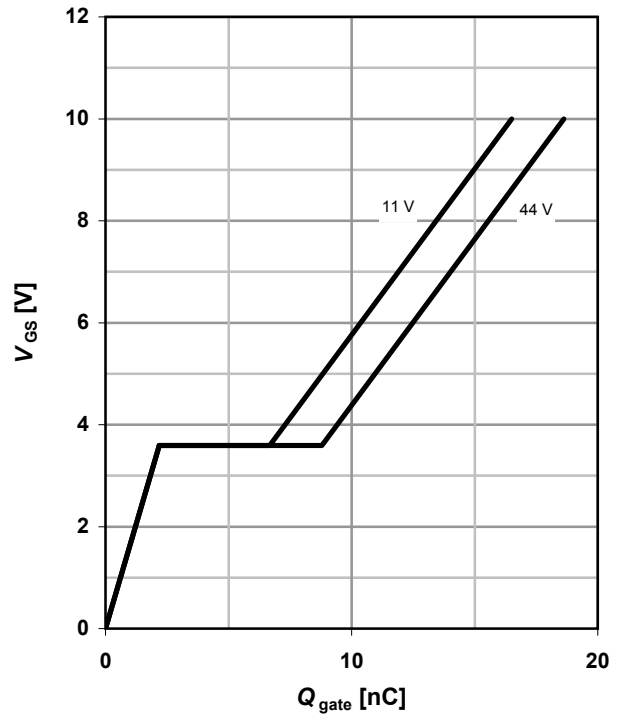
$E_{AS} = f(T_j)$

parameter:  $I_D$



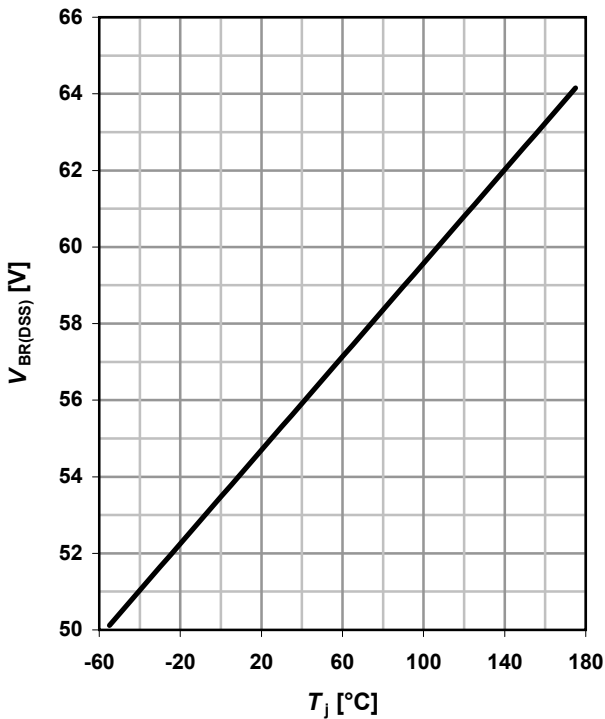
**14 Typ. gate charge**

$V_{GS} = f(Q_{gate}); I_D = 26 A$  pulsed

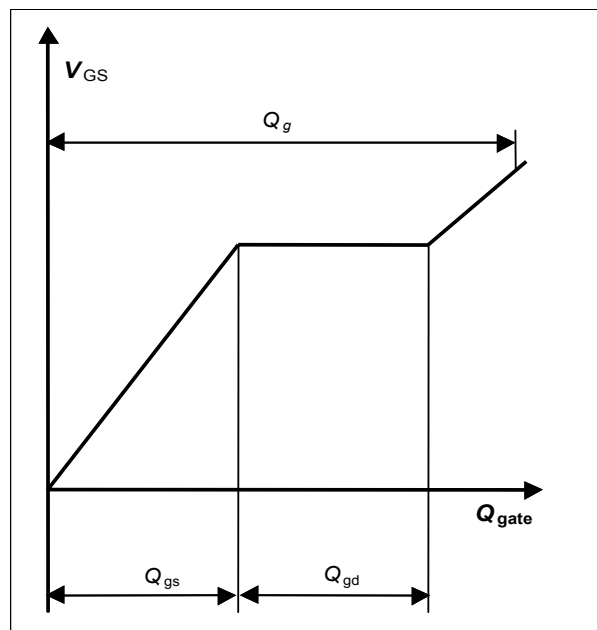


**15 Typ. drain-source breakdown voltage**

$V_{BR(DSS)} = f(T_j); I_D = 1 mA$



**16 Gate charge waveforms**



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